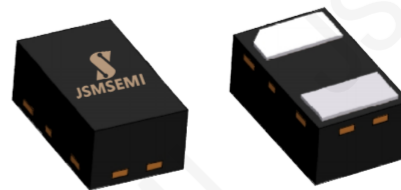


Diode Description

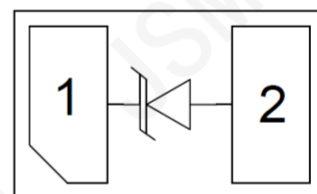
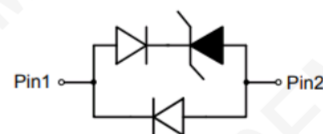
The ESD5341N is a Unidirectional TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive high-speed data lines. The ESD5341N has an ultra low capacitance with a typical value at 0.5 pF, and complies with the IEC 61000-4-2 (ESD) standard with $\pm 15\text{kV}$ air and $\pm 8\text{kV}$ contact discharge. It is assembled into an ultra-small 1.0x0.6x0.5mm lead-free DFN package. The small size, ultra-low capacitance and high ESD surge protection make ESD5341N an ideal choice to protect cell phone, digital video interfaces and other high.

Features

- ◆ Ultra small package: 1.0x0.6x0.5mm
- ◆ Ultra low capacitance: 0.5pF typical
- ◆ Ultra low leakage: nA level
- ◆ Low operating voltage: 5V
- ◆ Low clamping voltage
- ◆ 2-pin leadless package
- ◆ Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
 - Air discharge: $\pm 20\text{kV}$
 - Contact discharge: $\pm 15\text{kV}$
 - IEC61000-4-5 (Lightning) 4.5A (8/20 μs)
- ◆ RoHS Compliant
- ◆ Lead Finish: NiPdAu



DFN1006-2



Circuit Diagram

Applications

- ◆ Smart phones
- ◆ Display Ports
- ◆ MDDI Ports
- ◆ USB Ports
- ◆ Digital Video Interface (DVI)
- ◆ PCI Express and Serial SATA Ports

Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

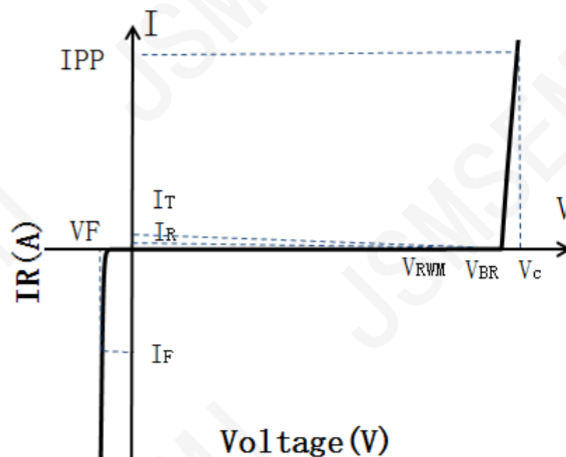
Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20 μs)	Ppk	80	W
Peak Pulse Current (8/20 μs)	IPP	4.5	A
ESD per IEC 61000-4-2 (Air)	VESD	± 22	kV
ESD per IEC 61000-4-2 (Contact)		± 22	
Operating Temperature Range	TJ	-55 to +125	$^{\circ}\text{C}$
Storage Temperature Range	Tstg	-55 to +150	$^{\circ}\text{C}$

Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

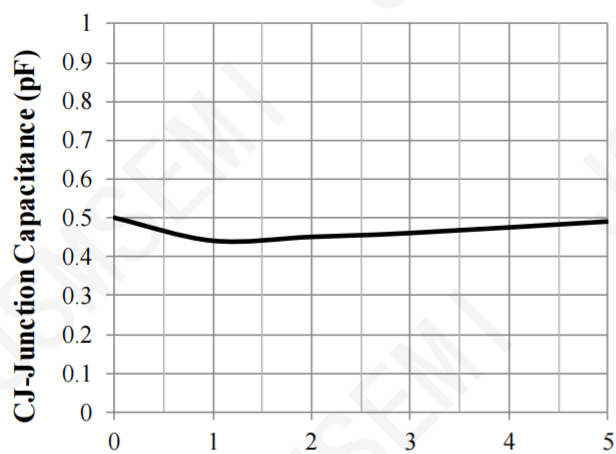
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse Working Voltage	VRWM				5.0	V
Breakdown Voltage	VBR	IT= 1mA	6.0	7.0	8.5	V
Reverse Leakage Current	IR	VRWM= 5.0V			0.2	μA
Clamping Voltage	VC	IPP= 1A (8 x 20 μs pulse)			9.0	V
Clamping Voltage	VC	IPP= 4.5A (8 x 20 μs pulse)			16	V
Junction Capacitance	CJ	VR = 0V, f = 1MHz		0.5	0.6	pF

Portion Electronics Parameter

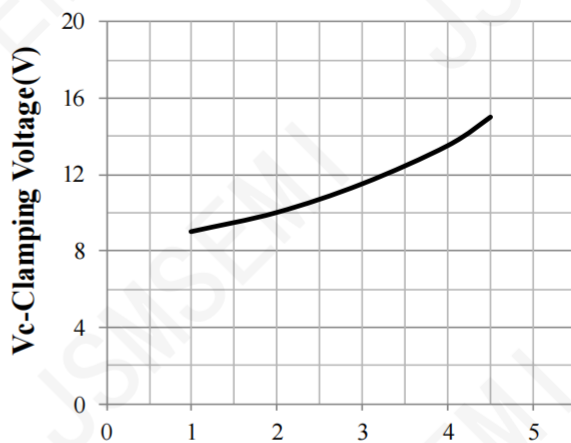
Symbol	Parameter
IT	Test Current
IPP	Maximum Reverse Peak Pulse Current
Vc	Clamping Voltage @Ic



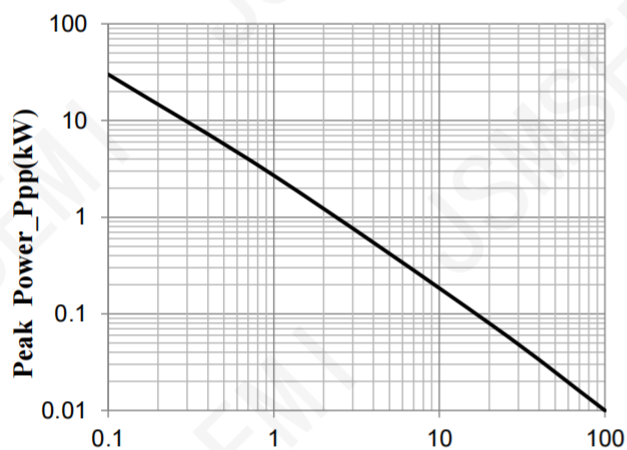
Typical Performance Characteristics (TA=25°C unless otherwise Specified)



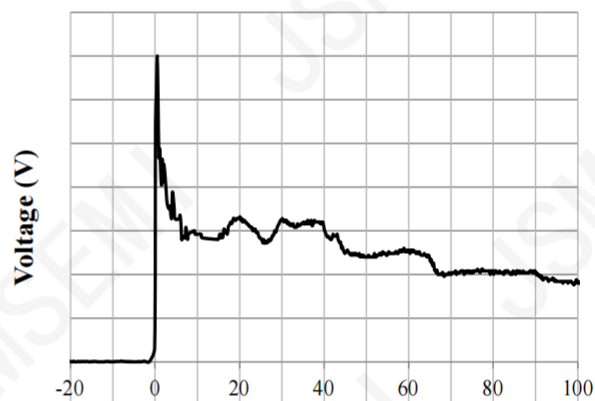
VR—Reverse Voltage (V)
Junction Capacitance vs. Reverse Voltage



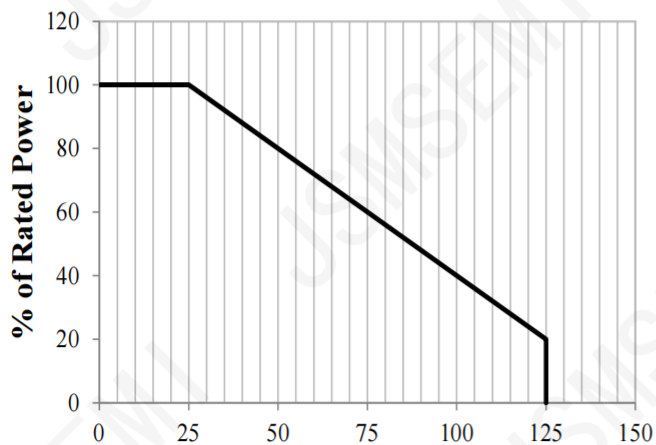
Ipp-Peak Pulse Current (A)
Clamping Voltage vs. Peak Pulse Current



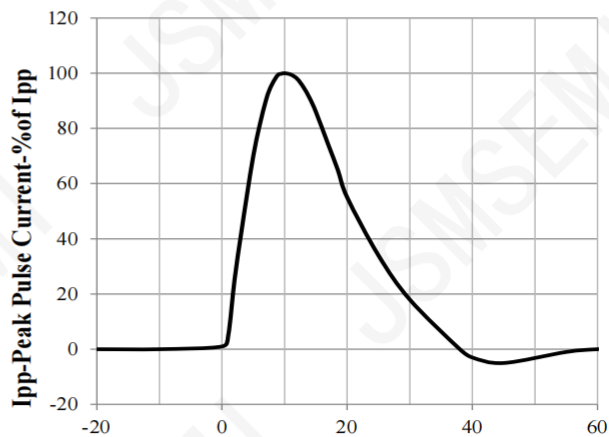
Pulse Duration tp (uS)
Peak Pulse Power vs. Pulse Time



Time (nS)
IEC61000-4-2 Pulse Waveform

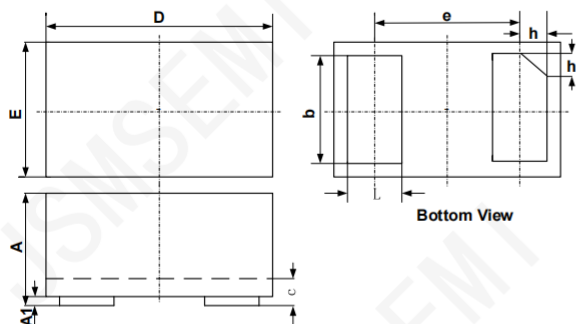


Ambient Temperature Ta (°C)
Power Derating Curve



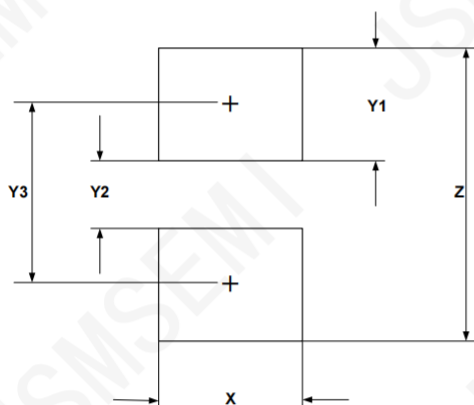
T-Time (us)
8 X 20us Pulse Waveform

DFN1006-2 Package Outline Drawing



SYM	DIMENSIONS					
	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.45	0.50	0.55	0.018	0.020	0.022
A1	0.00	0.02	0.05	0.000	0.001	0.002
b	0.45	0.50	0.55	0.018	0.020	0.022
c	0.12	0.15	0.18	0.005	0.006	0.007
D	0.95	1.00	1.05	0.037	0.039	0.041
e	0.65 BSC			0.026 BSC		
E	0.55	0.60	0.65	0.022	0.024	0.026
L	0.20	0.25	0.30	0.008	0.010	0.012
h	0.07	0.12	0.17	0.003	0.005	0.007

Suggested Land Pattern



SYM	DIMENSIONS	
	MILLIMETERS	INCHES
X	0.60	0.024
Y1	0.50	0.020
Y2	0.30	0.012
Y3	0.80	0.032
Z	1.30	0.052